

General Purpose Transistors

NPN Silicon

MMBT2222L, MMBT2222AL, SMMBT2222AL

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

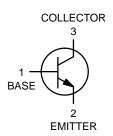
Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V _{CEO}	30 40	Vdc
Collector-Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V _{CBO}	60 75	Vdc
Emitter – Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	Ic	600	mAdc
Collector Current – Peak (Note 3)	I _{CM}	1100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Reference SOA curve.





SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



xxx = 1P or M1B M = Date Code* • = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc,	I _B = 0) MMBT2222 MMBT2222A	V _{(BR)CEO}	30 40	_ _	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc$, $I_E = 10 \mu Adc$)	= 0) MMBT2222 MMBT2222A	V _{(BR)CBO}	60 75	- -	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C =$	0) MMBT2222 MMBT2222A	V _{(BR)EBO}	5.0 6.0	- -	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MMBT2222A, SMMBT2222A	I _{CEX}	-	10	nAdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}$, $I_{E} = 0$) ($V_{CB} = 60 \text{ Vdc}$, $I_{E} = 0$) ($V_{CB} = 50 \text{ Vdc}$, $I_{E} = 0$, $T_{A} = 125^{\circ}\text{C}$) ($V_{CB} = 60 \text{ Vdc}$, $I_{E} = 0$, $T_{A} = 125^{\circ}\text{C}$)	MMBT2222 MMBT2222A, SMMBT2222A MMBT2222 MMBT2222A, SMMBT2222A	Ісво	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	MMBT2222A, SMMBT2222A	I _{EBO}	-	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MMBT2222A, SMMBT2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS		•			
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_A=-55^{\circ}\text{C}) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc) (Note 4)} \\ (I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc) (Note 4)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc) (Note 4)} \\ \end{array} $	MMBT2222A only MMBT2222 MMBT2222A, SMMBT2222A	h _{FE}	35 50 75 35 100 50 30 40	- - - 300 - -	-
Collector – Emitter Saturation Voltage (Note 4) (I _C = 150 mAdc, I _B = 15 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A	V _{CE(sat)}	- -	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT2222 MMBT2222A, SMMBT2222A		- -	1.6 1.0	
Base – Emitter Saturation Voltage (Note 4) $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$	MMBT2222 MMBT2222A, SMMBT2222A	V _{BE(sat)}	_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT2222 MMBT2222A, SMMBT2222A		- -	2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Note 5) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	MMBT2222 MMBT2222A, SMMBT2222A	f⊤	250 300	- -	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C _{obo}	_	8.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	MMBT2222 MMBT2222A, SMMBT2222A	C _{ibo}	- -	30 25	pF
Input Impedance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
$\begin{split} &\text{Small-Signal Current Gain} \\ &\text{(I}_{\text{C}} = 1.0 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \\ &\text{(I}_{\text{C}} = 10 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc, f} = 1.0 \text{ kHz)} \end{split}$	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h _{fe}	50 75	300 375	_

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS			•		•
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kH}$ ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$		h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8 MHz) MMBT2222A, SMMBT2222A		rb, C _c	-	150	ps
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz) MMBT2222A, SMMBT2222A		NF	-	4.0	dB
SWITCHING CHARACTERISTICS (MMBT2	222A only)		•		•
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$	t _d	_	10	
Rise Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc}, \\ I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$	t _r	_	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,	t _s	-	225	
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$	t _f	_	60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 5. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

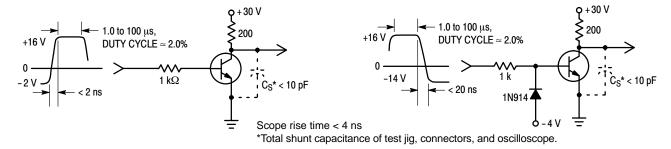


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

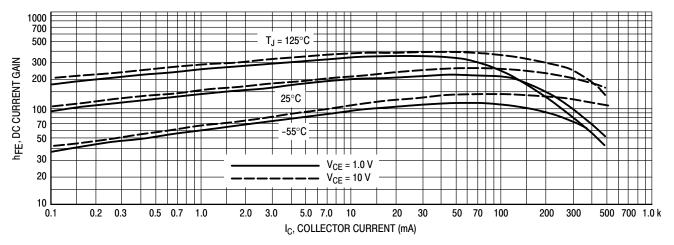


Figure 3. DC Current Gain

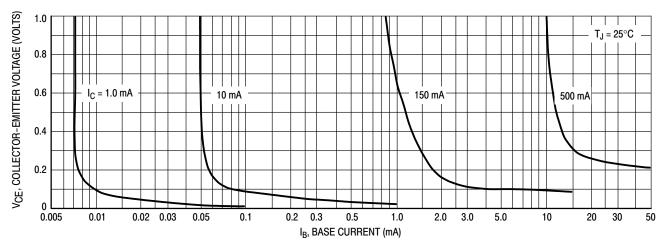


Figure 4. Collector Saturation Region

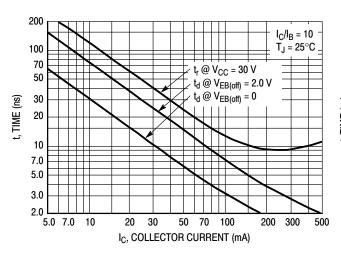


Figure 5. Turn-On Time

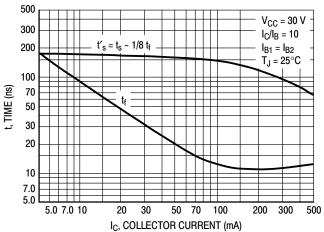


Figure 6. Turn-Off Time

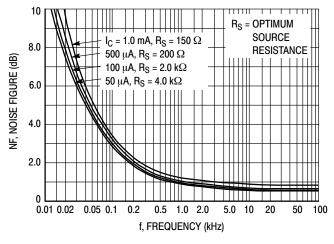


Figure 7. Frequency Effects

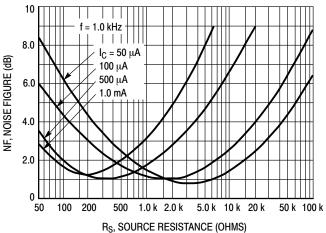
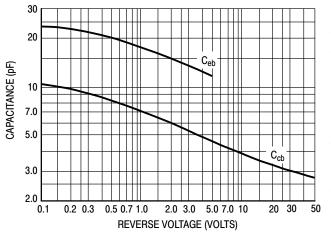


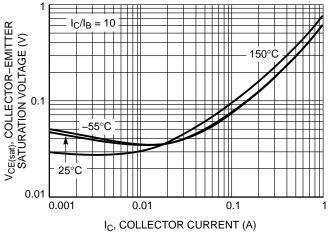
Figure 8. Source Resistance Effects



f_T, CURRENT-GAIN BANDWIDTH PRODUCT (MHz) 500 V_{CE} = 20 V $T_J = 25^{\circ}C$ 300 200 100 70 50 70 100 1.0 2.0 3.0 5.0 7.0 20 50 IC, COLLECTOR CURRENT (mA)

Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product



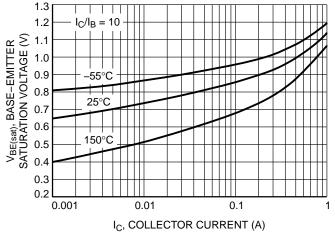
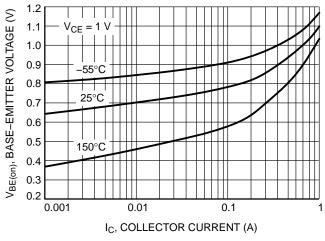


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Saturation Voltage vs.
Collector Current



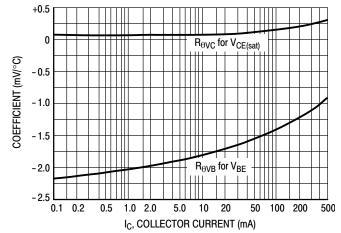


Figure 13. Base Emitter Voltage vs. Collector Current

Figure 14. Temperature Coefficients

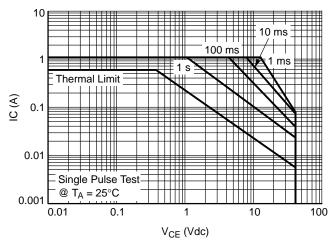


Figure 15. Safe Operating Area

ORDERING INFORMATION

Device	Specific Marking Code	Package	Shipping [†]
MMBT2222LT1G	M1B	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222ALT1G, SMMBT2222ALT1G	1P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222LT3G	M1B	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT2222ALT3G, SMMBT2222ALT3G	1P	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

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